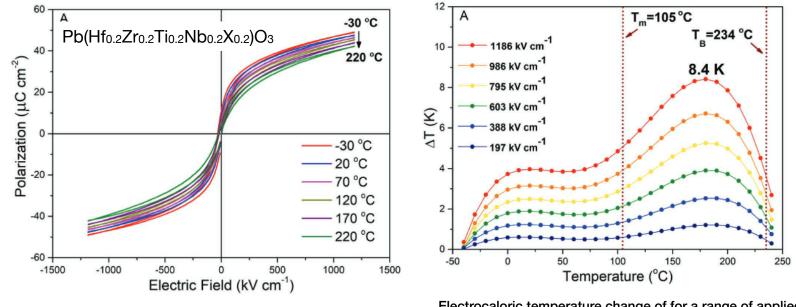
## **Electrocaloric Effect of Perovskite High Entropy Oxide Films**

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Pb(Hf<sub>0.2</sub>Zr<sub>0.2</sub>Ti<sub>0.2</sub>Nb<sub>0.2</sub>X<sub>0.2</sub>)O<sub>3</sub>, a high-entropy perovskite, undergoes an entropy-driven phase transformation when X=Mn while X=AI always contains minor second phases in bulk ceramics. Thin films with X=AI show a narrow ferroelectric hysteresis loop and relaxor-like characteristics, i.e. a high dielectric permittivity of ~2000 and low dielectric loss. These are the characteristics needed for device applications.



Narrow hysteresis loop indicating relaxor behavior.

Electrocaloric temperature change of for a range of applied electric fields  $\Delta E = E_2 - E_1$  with  $E_2 = 1186$  kV cm<sup>-1</sup>.

Indirect measurements (based on Maxwell relations) yield a electrocaloric temperature change of 8.4 K at 180°C under an applied electric field of 1186 kV cm<sup>-1</sup>. The temperature changes in this initial example of a high-entropy electrocaloric oxide are already comparable to those of other oxidebased materials. The huge design space available for optimization of high-entropy formulations now offers opportunities to exceed known electrocalorics in terms of both size of response and operating temperature range.



